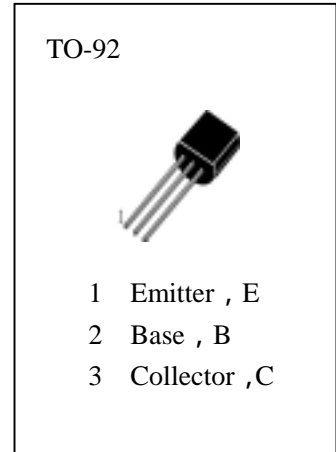




HIGH VOLTAGE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (Ta=25)

- T_{stg}—Storage Temperature..... -55~150
- T_j—Junction Temperature.....150
- P_C—Collector Dissipation.....625mW
- V_{CBO}—Collector-Base Voltage.....-400V
- V_{CEO}—Collector-Emitter Voltage.....-400V
- V_{EBO}—Emitter-Base Voltage.....-6V
- I_C—Collector Current.....-300mA



ELECTRICAL CHARACTERISTICS (Ta=25)

| Symbol | Characteristics | Min | Typ | Max | Unit | Test Conditions |
|-----------|---------------------------------------|------|-----|-------|------|---|
| BVCBO | Collector-Base Breakdown Voltage | -400 | | | V | I _C =-100 μ A, I _E =0 |
| BVCES | Collector-Emitter Breakdown Voltage | -400 | | | V | I _C =-100 μ A, V _{BE} =0 |
| BVEBO | Emitter-Base Breakdown Voltage | -6 | | | V | I _E =-10 μ A , I _C =0 |
| ICBO | Collector Cut-off Current | | | -100 | nA | V _{CB} =-300V, I _E =0 |
| IEBO | Emitter-Base Cut-off Current | | | -100 | nA | V _{EB} =-4V, I _C =0 |
| ICES | Collector Cut-off Current | | | -1 | μ A | V _{CE} =-400V, V _{BE} =0 |
| HFE (1) | DC Current Gain | 40 | | | | V _{CE} =-10V, I _C =-1mA |
| HFE (2) | | 60 | | 300 | | V _{CE} =-10V, I _C =-10mA |
| HFE (3) | | 45 | | | | V _{CE} =-10V, I _C =-50mA |
| HFE (4) | | 40 | | | | V _{CE} =-10V, I _C =-100mA |
| VCE(sat1) | Collector- Emitter Saturation Voltage | | | -0.5 | V | I _C =-10mA, I _B =-1mA |
| VCE(sat2) | | | | -0.75 | V | I _C =-50mA, I _B =-5mA |
| VBE(sat) | Base-Emitter Saturation Voltage | | | -0.75 | V | I _C =-10mA, I _B =-1mA |
| Cob | Output Capacitance | 7 | | | pF | V _{CB} =20V, I _E =0 ,F=1MHz |